

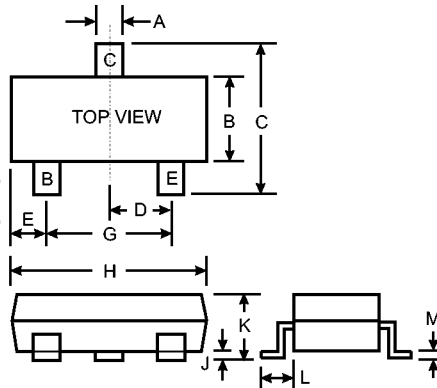
Features

- 310 mW Power Dissipation
- Ideally Suited for Automatic Insertion
- Epitaxial Planar Die Construction
- For Switching, AF Driver and Amplifier Applications
- Complementary PNP Types Available (BC807)

Mechanical Data

- Case: SOT-23, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Pin Connections: See Diagram
- Marking:

BC817-16	6A
BC817-25	6B
BC817-40	6C
- Aprox. Weight: 0.008 grams
- Mounting Position: Any



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.19	1.40
C	2.10	2.50
D	0.89	1.05
E	0.45	0.61
G	1.78	2.05
H	2.65	3.05
J	0.013	0.15
K	0.89	1.10
L	0.45	0.61
M	0.076	0.178
All Dimensions in mm		

Maximum Ratings @25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	800	mA
Peak Collector Current	I_{CM}	1000	mA
Peak Emitter Current	I_{EM}	1000	mA
Power Dissipation at $T_{SB} = 50^\circ\text{C}$ (Note 1)	P_d	310	mW
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	$^\circ\text{C}$

Electrical Characteristics @25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
DC Current Gain	h_{FE}	100	250	—	$V_{CE} = 1.0\text{V}, I_C = 100\text{mA}$
		160	400		
		250	600		
		60	—		
Current Gain Group -16	h_{FE}	100	—	—	$V_{CE} = 1.0\text{V}, I_C = 300\text{mA}$
		100	—		
		170	—		
Thermal Resistance, Junction to Substrate Backside	$R_{\theta SB}$	—	320	K/W	Note 1
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	—	400	K/W	Note 1
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.7	V	$I_C = 500\text{mA}, I_B = 50\text{mA}$
Base-Emitter Voltage	V_{BE}	—	1.2	V	$V_{CE} = 1.0\text{V}, I_C = 300\text{mA}$
Collector-Emitter Cutoff Current	I_{CES}	—	100	nA	$V_{CE} = 45\text{V}$
			5.0	μA	$V_{CE} = 25\text{V}, T_j = 150^\circ\text{C}$
Emitter-Base Cutoff Current	I_{EBO}	—	100	nA	$V_{EB} = 4.0\text{V}$
Gain Bandwidth Product	f_T	100	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}, f = 50\text{MHz}$
Collector-Base Capacitance	C_{CBO}	—	12	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$

Notes: 1. Device mounted on Ceramic Substrate 0.7mm; 2.5cm² area.

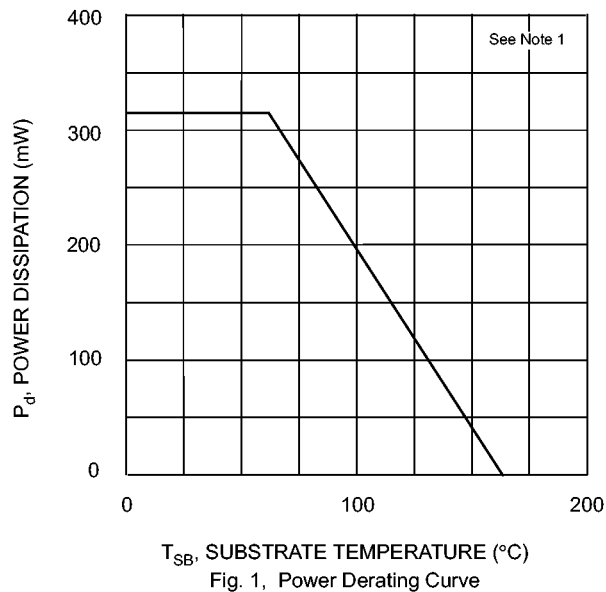


Fig. 1, Power Derating Curve

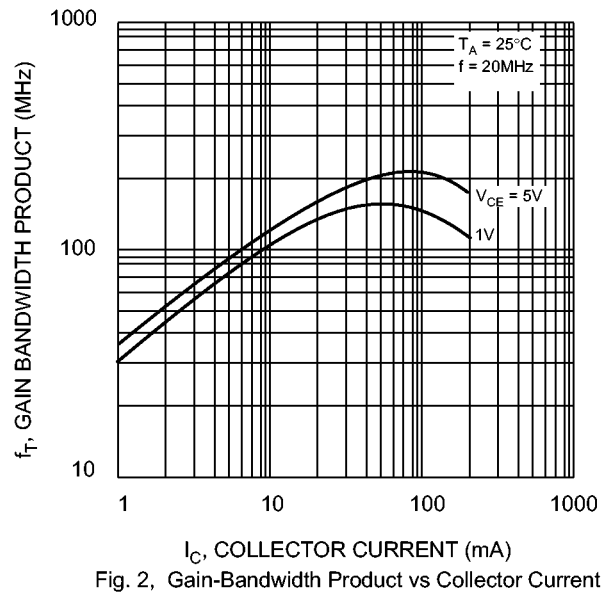


Fig. 2, Gain-Bandwidth Product vs Collector Current

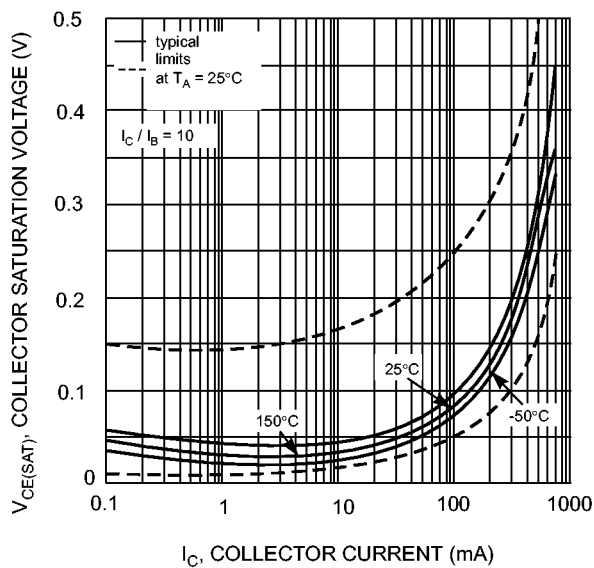


Fig. 3, Collector Sat. Voltage vs Collector Current

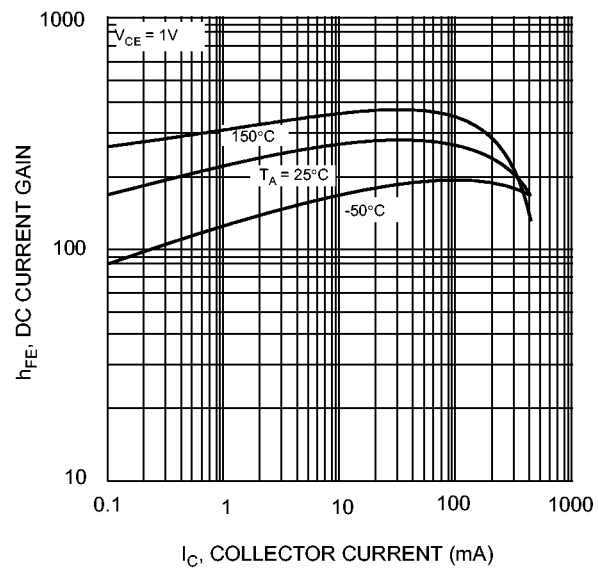


Fig. 4, DC Current Gain vs Collector Current

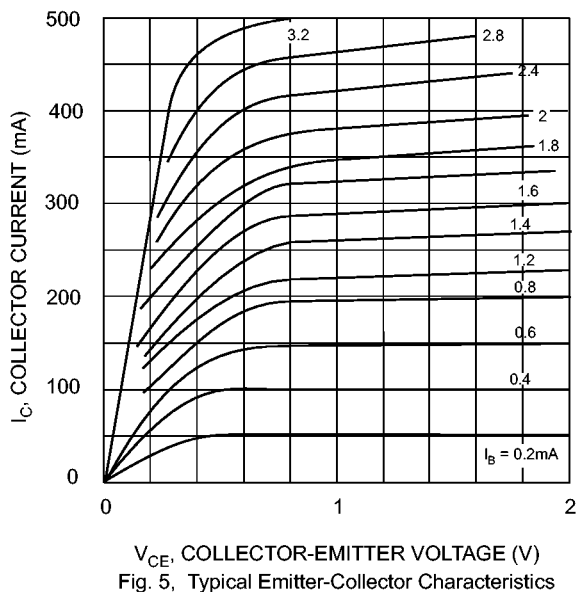


Fig. 5, Typical Emitter-Collector Characteristics

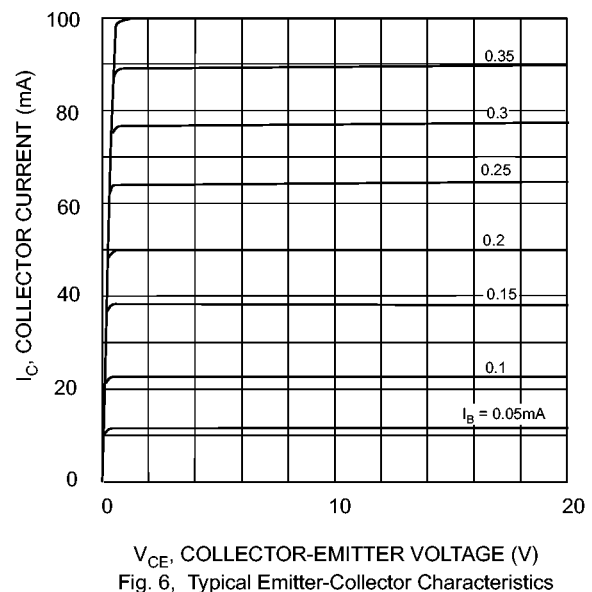


Fig. 6, Typical Emitter-Collector Characteristics